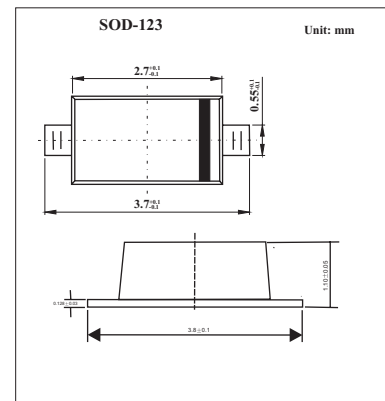


## Schottky Barrier Diode

### RB160M-30

#### ■ Features

- Small power mold type.
- Low  $I_R$
- High reliability



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

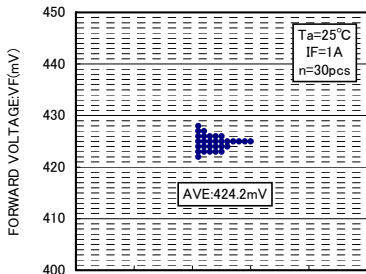
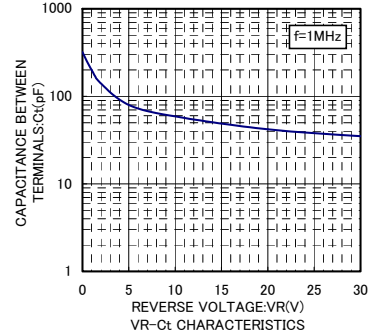
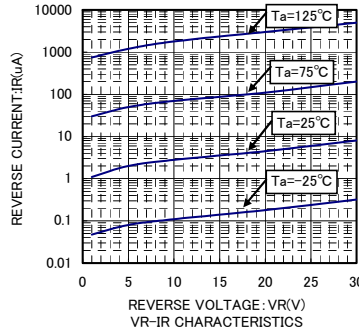
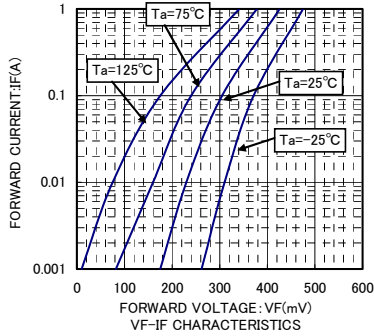
Parameter	Symbol	Rating	Unit
Reverse voltage	$V_{RM}$	30	V
reverse voltage	$V_R$	30	V
Forward current surge peak	$I_o$	1	A
Average rectified forward current	$I_{FSM}$	30	A
operating junction temperature	$T_j$	125	$^\circ\text{C}$
storage temperature	$T_{stg}$	-40 to +150	$^\circ\text{C}$

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

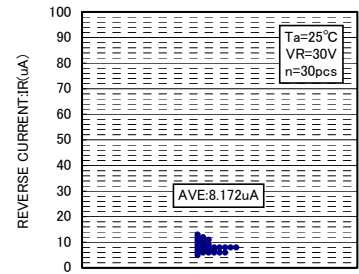
Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Forward voltage	$V_{F1}$	$I_F=0.5\text{A}$		0.39	0.46	V
	$V_{F2}$	$I_F=1.0\text{A}$		0.43	0.48	V
Reverse current	$I_{R1}$	$V_R=15\text{V}$		3.0	20	$\mu\text{A}$
	$I_{R2}$	$V_R=30\text{V}$		9.0	50	$\mu\text{A}$

# RB160M-30

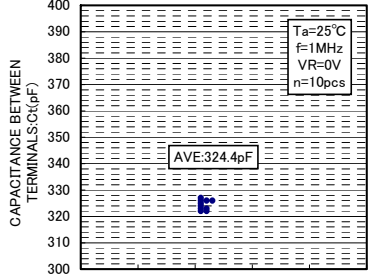
●Electrical characteristic curves (Ta=25°C)



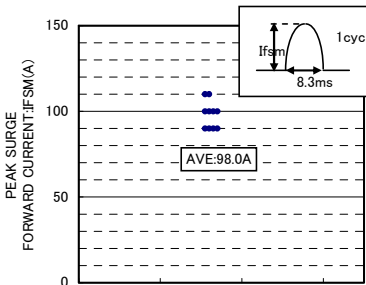
VF DISPERSION MAP



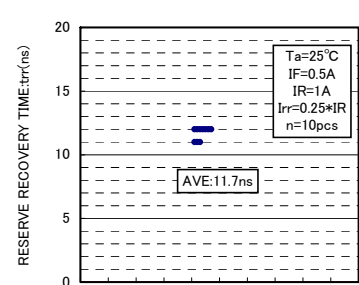
IR DISPERSION MAP



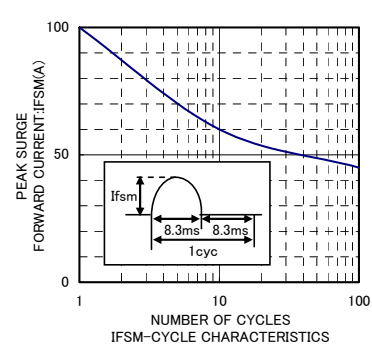
Ct DISPERSION MAP



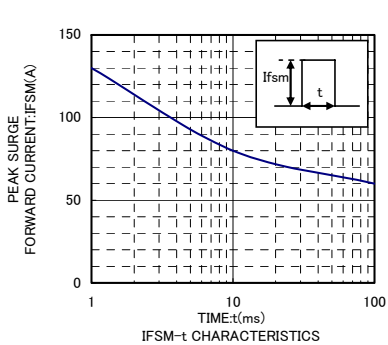
IFSM DISERSION MAP



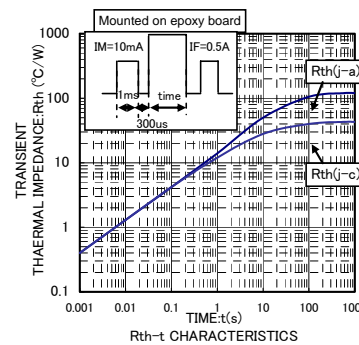
trr DISPERSION MAP



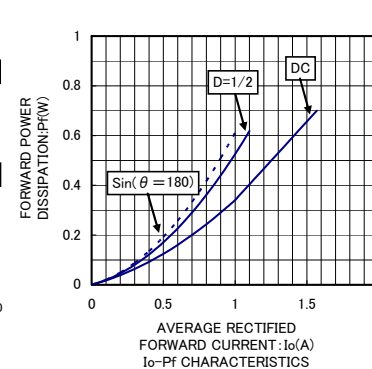
IFSM-CYCLE CHARACTERISTICS



IFSM-t CHARACTERISTICS



Rth-t CHARACTERISTICS



Io-PF CHARACTERISTICS